

**Amendments to the Claims**

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

**Listing of Claims:****Claims 1-10. (Canceled)**

11. (Currently Amended) A memory device comprising:

a recording film including at least one element selected from the group consisting of Ge and Sb, Te of 40 atom percent or more, and at least one element selected from Zn and Cd of 25 atom percent to 35 atom percent, said recording film being adapted to record information by causing a reversible phase change between a crystal phase and an amorphous phase;

and

an electrode adapted to apply a voltage to said recording film,

wherein a content of Sb is 25 atom percent to 35 atom percent.

**Claim 12. (Canceled)**

13. (Previously Presented) The memory device according to claim 11, wherein said device is adapted to be operable in an atmosphere at 140°C or more.

14. (Previously Presented) The memory device according to claim 11, having a region in which Zn or Cd content is relatively more than

that of said recording film by more than 10 atom percent, said region being located between said recording film and an electrode.

15. (Currently Amended) The memory device according to ~~claim 11~~ claim 20, wherein said region has a ~~multiplayer~~ multilayer structure with electrodes for voltage application and is adapted to transmit 30 percent or more of a recording light or reproduction light which is applied to it.

16. (Currently Amended) A memory device comprising:

a plurality of memory cells;

a plurality of word lines adapted to select said plurality of memory cells; and

a plurality of data lines placed to be orthogonal to said plurality of word lines and having signals read thereto from said plurality of memory cells, and

wherein each of said plurality of memory cells comprises a recording film of Ge and Sb, Te of 40 atom percent or more, and at least one element selected from Zn and Cd of 25 atom percent to 35 atom percent, said recording film being adapted to record information by causing a reversible phase change between a crystal phase and an amorphous phase, and an electrode adapted to apply a voltage to said recording film,

wherein a content of Sb is 25 atom percent to 35 atom percent.

17. (Previously Presented)      The memory device according to claim 16, wherein an insulating film is provided between said recording film and said electrode.

18. (Previously Presented)      The memory device according to claim 12, wherein both of the Ge and Sb are included and the ratio between Ge and Sb is in the range of 1:2 to 2:1.

**Claim 19. (Canceled)**

20. (New)      A memory device comprising:

        a recording film including at least one element selected from the group consisting of Ge and Sb, Te of 40 atom percent or more, and at least one element selected from Zn and Cd of 25 atom percent to 35 atom percent, said recording film being adapted to record information by causing a reversible phase change between a crystal phase and an amorphous phase;

        an electrode adapted to apply a voltage to said recording film, and

        a region in which Zn or Cd content is relatively more than that of said recording film by more than 10 atom percent, said region being located between said recording film and an electrode.